

**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

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FIS9-2001-0 295-US2

SERIAL NO. Divisional of  
10/047,964

Tze-Chiang Chen et al.

FILING 8-24-03  
8/27/03

GROUP 5250 2825

10-650890

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CL	6,043,152	03/28/2000	Chang et al.			
	6,080,529	06/27/2000	Ye et al.			
	6,099,701	08/08/2000	Liu et al.			
	6,107,188	08/22/2000	Liu et al.			
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
CL ✓	WO 00/19523	06/06/2000	CA,CN,JP, European Patent				
✓	JP2001015480A	01/19/2001	Japan				
✓	JP2001053076A	02/23/2001	Japan				
✓	JP1111843A	04/28/1989	Japan				
CL	WO 99/33102	07/01/1999	JP,KR, European Patent				

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CL	J	Soo Geun Lee et al., "Low Dielectric Constant 3MS a-SiC:H as Cu Diffusion Barrier Layer in Cu Dual Damascene Process," Japanese Journal of Applied Physics, Part 1, Vol. 40, No. 4B, pp. 2663-2668, April 2001.
CL	J	R.D. Goldblatt et al., "A High Performance 0.13 um Copper BEOL Technology with Low-k Dielectric," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 261-263, June 5-7, 2000.

EXAMINER

calvonee

DATE CONSIDERED

7.26.04

"EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant."

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. FIS9-2001-0295- US2	SERIAL NO. <i>Divisional of 10/047,964</i> <b>10-650890</b>		
				Tze-Chiang Chen et al.			
				FILING <i>8-28-03 8-27-03</i>	GROUP <i>2805 5350</i>		
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>CL</i>		6,261,951 B1	07/17/2001	Buchwalter et al.			
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
<i>CL</i>	<i>/</i>	<i>J. Yota et al., "Comparison Between HDP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 76-78, June 5-7, 2000.</i>					
EXAMINER <i>calonla</i>				DATE CONSIDERED <i>7.26.04</i>			
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